

Please replace the paragraph at page 9 lines 9 through 17 with the following rewritten paragraph.

A2 - - Fig. 4A is a scanning electron microscope (SEM) graph of a metal gate electrode which is comprised of polysilicon-tungsten nitride-tungsten and formed by a method in according to the conventional art. The metal gate electrode is formed by forming a metal gate electrode pattern, performing a selective oxidation process in accordance with the conventional oxidation process and heating the metal gate electrode pattern. The graph is taken after performing the heating process to examine the whiskers. Figs. 4B and 4C are SEM graphs of a metal gate electrode which is formed using a selective oxidation process in accordance with the present invention.- -

In the Claims

Please amend the claims as follows:

- A3
5. (Amended) The method according to claim 1, wherein oxygen gas and hydrogen are used as a source gas in the selective oxidation process.

Please add the following new claims:

- A4
6. (New) The method according to claim 2, wherein oxygen gas and hydrogen are used as a source gas in the selective oxidation process.
 7. (New) The method according to claim 3, wherein oxygen gas and hydrogen are used as a source gas in the selective oxidation process.
 8. (New) The method according to claim 4, wherein oxygen gas and hydrogen are used as a source gas in the selective oxidation process.